

Mohamed Abdelhedi,^{a,b}
 Mohamed Dammak,^{b*} Alain
 Cousson,^a Martine Nierlich^c and
 Kolsi Abdelwaheb^b

^aLaboratoire Léon Brillouin, CE/Saclay, Bât. 563, 91191 Gif-sur-Yvette Cedex, France,

^bLaboratoire de l'Etat Solide, Faculté des Sciences de Sfax, 3018 Sfax, Tunisia, and ^cSCM, CE/Saclay, Bât. 125, 91191 Gif-sur-Yvette Cedex, France

Correspondence e-mail: meddammak@yahoo.fr

Key indicators

Single-crystal X-ray study

$T = 298\text{ K}$

Mean $\sigma(\text{S}-\text{O}) = 0.009\text{ \AA}$

H-atom completeness 0%

Disorder in main residue

R factor = 0.037

wR factor = 0.035

Data-to-parameter ratio = 10.7

For details of how these key indicators were automatically derived from the article, see <http://journals.iucr.org/e>.

$\text{Cs}_2(\text{SO}_4)_{0.57}(\text{SeO}_4)_{0.43}\cdot\text{Te}(\text{OH})_6$, an adduct between dicaesium sulfate selenate and telluric acid

The title compound, dicaesium sulfate selenate–telluric acid adduct, $\text{Cs}_2(\text{SO}_4)_{0.57}(\text{SeO}_4)_{0.43}\cdot\text{Te}(\text{OH})_6$, is a solid solution in the series $\text{Cs}_2(\text{SO}_4)\cdot\text{Te}(\text{OH})_6/\text{Cs}_2(\text{SeO}_4)\cdot\text{Te}(\text{OH})_6$. It crystallizes in the same structure as the end member $\text{Cs}_2(\text{SeO}_4)\cdot\text{Te}(\text{OH})_6$ in space group $P2_1/c$, whereas the corresponding sulfate adopts another structure type and crystallizes in space group $R3$. The structure contains planes of statistically distributed SO_4/SeO_4 tetrahedra alternating with planes of $\text{Te}(\text{OH})_6$ octahedra, and with Cs^+ cations situated between the planes. Both Te atoms lie on centres of symmetry.

Received 16 September 2005

Accepted 24 October 2005

Online 31 October 2005

Comment

Pursuing our study of adducts between sulfate and/or selenate salts with telluric acid, among which we have solved the crystal structures of $\text{Cs}_2\text{SO}_4\cdot\text{Te}(\text{OH})_6$, $\text{Cs}_2\text{SeO}_4\cdot\text{Te}(\text{OH})_6$ (Dammak *et al.*, 2001) and $\text{Rb}_2(\text{SO}_4)_{0.5}(\text{SeO}_4)_{0.5}\cdot\text{Te}(\text{OH})_6$ (Abdelhedi *et al.*, 2005), we have grown crystals of $\text{Cs}_2(\text{SO}_4)_{0.57}(\text{SeO}_4)_{0.43}\cdot\text{Te}(\text{OH})_6$, (I), from a solution of Cs_2SO_4 , Cs_2SeO_4 and telluric acid.

Compound (I) is a solid solution in the series $\text{Cs}_2(\text{SO}_4)\cdot\text{Te}(\text{OH})_6/\text{Cs}_2(\text{SeO}_4)\cdot\text{Te}(\text{OH})_6$ and crystallizes in the same space group as the end member $\text{Cs}_2(\text{SeO}_4)\cdot\text{Te}(\text{OH})_6$, whereas the sulfate end member adopts another structure type in space group $R3$ (Dammak *et al.*, 2001). In (I), the S and Se atoms are statistically distributed over the same site. The crystal structure can be regarded as being built up of planes of $\text{Te}(\text{OH})_6$ octahedra (at $x = 0$ and $\frac{1}{2}$) alternating with planes of XO_4 tetrahedra (at $x = \frac{1}{4}$ and $\frac{3}{4}$; $X = \text{S}$ and Se), with Cs^+ cations intercalated between the planes (Figs. 1 and 2). In the XO_4 tetrahedra, the $X-\text{O}$ distances range from 1.511 (9) Å to

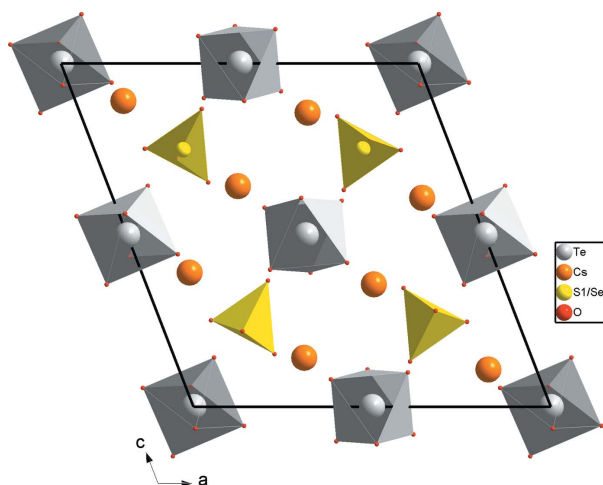
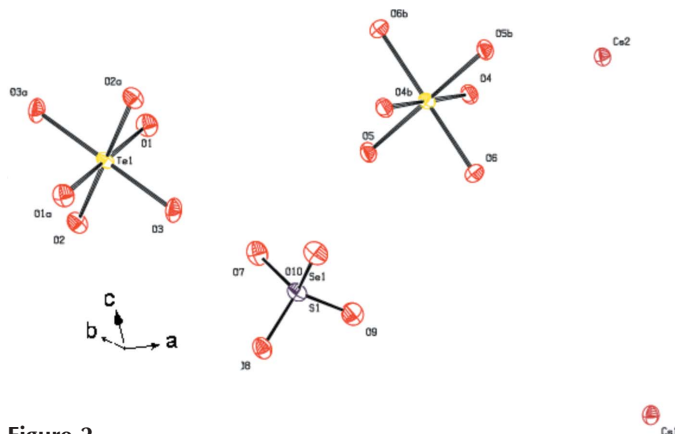


Figure 1
 Projection of the crystal structure of (I) on to the ac plane.

**Figure 2**

Part of the crystal structure of (I), with displacement parameters drawn at the 50% probability level. [Symmetry codes: (a) $-x, -y, 1-z$; (b) $1-x, 1-y, 1-z$.]

1.558 (9) Å, intermediate between those observed in the end members $\text{Cs}_2\text{SO}_4\cdot\text{Te}(\text{OH})_6$ [1.399 (10)–1.405 (7) Å] and $\text{Cs}_2\text{SeO}_4\cdot\text{Te}(\text{OH})_6$ [1.630 (4)–1.649 (4) Å; Dammak *et al.*, 2001]. The Te atoms occupy two sites, giving rise to two kinds of octahedra, *viz.* Te1O_6 and Te2O_6 , having bond lengths and angles similar to those in $\text{K}_2\text{SO}_4\cdot\text{Te}(\text{OH})_6$ (Zilber *et al.*, 1980) and $\text{Tl}_2\text{SO}_4\cdot\text{Te}(\text{OH})_6$ (Zilber *et al.*, 1982) (Table 1). The coordination environments around both Cs cations are slightly different, with Cs1 having ten coordination partners and Cs2 having 11 coordination partners (Table 1; Figs. 3 and 4). In contrast, the Rb cations in $\text{Rb}_2(\text{SO}_4)_{0.5}(\text{SeO}_4)_{0.5}\cdot\text{Te}(\text{OH})_6$ (Abdelhedi *et al.*, 2005) and the Cs cations in $\text{Cs}_2\text{SeO}_4\cdot\text{Te}(\text{OH})_6$ (Dammak *et al.*, 2001) are ninefold coordinate.

Experimental

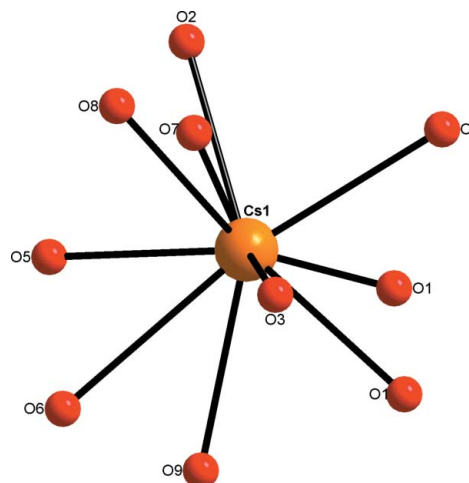
Crystals were grown at room temperature by evaporating an aqueous solution of telluric acid, H_6TeO_6 (Aldrich, 99%), caesium carbonate, Cs_2CO_3 (Aldrich 99.9%), selenic acid, H_2SeO_4 (Aldrich 94%) and caesium sulfate Cs_2SO_4 , (Aldrich 99.999%) (in the stoichiometric ratio 1:0.5:0.5:0.5). After a few days, colourless single crystals of $\text{Cs}_2(\text{SO}_4)_{0.57}(\text{SeO}_4)_{0.43}\cdot\text{Te}(\text{OH})_6$ were obtained.

Crystal data

$\text{Cs}_2(\text{SO}_4)_{0.57}(\text{SeO}_4)_{0.43}\cdot\text{Te}(\text{OH})_6$	$D_x = 3.765 \text{ Mg m}^{-3}$
$M_r = 611.68$	Mo $K\alpha$ radiation
Monoclinic, $P2_1/c$	Cell parameters from 986 reflections
$a = 12.2646$ (4) Å	$\theta = 1.8\text{--}25.8^\circ$
$b = 7.3926$ (4) Å	$\mu = 11.12 \text{ mm}^{-1}$
$c = 12.6354$ (6) Å	$T = 298 \text{ K}$
$\beta = 111.095$ (3)°	Prism, colourless
$V = 1068.84$ (9) Å ³	$0.10 \times 0.05 \times 0.05 \text{ mm}$
$Z = 4$	

Data collection

Nonius KappaCCD diffractometer	1881 independent reflections
φ scans	1216 reflections with $I > 3\sigma(I)$
Absorption correction: multi-scan (using intensity measurements)	$R_{\text{int}} = 0.042$
MULABS in PLATON (Spek, 2003)	$\theta_{\text{max}} = 25.8^\circ$
$T_{\text{min}} = 0.541, T_{\text{max}} = 0.573$	$h = -14 \rightarrow 14$
2044 measured reflections	$k = -8 \rightarrow 0$
	$l = 0 \rightarrow 14$

**Figure 3**

The coordination of Cs1.

Refinement

Refinement on F	$(\Delta/\sigma)_{\text{max}} < 0.001$
$R[F^2 > 2\sigma(F^2)] = 0.037$	$\Delta\rho_{\text{max}} = 2.43 \text{ e \AA}^{-3}$
$wR(F^2) = 0.035$	$\Delta\rho_{\text{min}} = -2.54 \text{ e \AA}^{-3}$
$S = 0.94$	Extinction correction: Larson (1970)
1216 reflections	Extinction coefficient: 17.2 (14)
114 parameters	
H-atom parameters not refined	
Weighting scheme: Chebyshev polynomial (Watkin, 1994; Prince, 1982)	
$w = [1 - (F_o^2 - F_c^2)/36\sigma^2(F_o)] / [2.38T_0(x) - 2.95T_1(x) + 2.50T_2(x) - 1.02T_3(x) + 0.340T_4(x)]$, where $x = F/F_{\text{max}}$;	
robust weighting (Prince, 1982)	

Table 1

Selected geometric parameters (Å, °).

X is disordered S/Se on a single site.

Te1—O1 ⁱ	1.935 (8)	Cs1—O8 ^{iv}	3.334 (9)
Te1—O2 ⁱ	1.917 (8)	Cs1—O1 ^{viii}	3.413 (9)
Te1—O3 ⁱ	1.896 (8)	Cs1—O6 ^{viii}	3.460 (9)
Te2—O4 ⁱⁱ	1.937 (8)	Cs1—O7 ⁱⁱⁱ	3.698 (8)
Te2—O6 ⁱⁱ	1.925 (8)	Cs2—O6 ^{ix}	3.098 (8)
Te2—O5 ⁱⁱ	1.905 (8)	Cs2—O4	3.109 (8)
X1—O7	1.511 (9)	Cs2—O2 ^s	3.133 (9)
X1—O8	1.526 (8)	Cs2—O3 ⁱⁱ	3.153 (9)
X1—O9	1.558 (9)	Cs2—O9 ^{iv}	3.165 (9)
X1—O10	1.546 (8)	Cs2—O8 ^{vi}	3.248 (9)
Cs1—O5 ⁱⁱⁱ	2.988 (9)	Cs2—O4 ^{iv}	3.301 (8)
Cs1—O1 ⁱⁱⁱ	3.065 (9)	Cs2—O5 ^{iv}	3.337 (8)
Cs1—O3 ^{iv}	3.116 (9)	Cs2—O10 ⁱⁱ	3.404 (8)
Cs1—O2 ^v	3.147 (9)	Cs2—O10 ^{ix}	3.639 (10)
Cs1—O7 ^v	3.255 (9)	Cs2—O6 ^{iv}	3.675 (9)
Cs1—O9 ^{vi}	3.292 (9)		
O1 ⁱ —Te1—O2 ⁱ	86.5 (4)	O6 ⁱⁱ —Te2—O4	92.1 (4)
O1 ⁱ —Te1—O3 ⁱ	91.3 (4)	O5 ⁱⁱ —Te2—O4	91.5 (3)
O2 ⁱ —Te1—O3 ⁱ	88.5 (4)	O6 ⁱⁱ —Te2—O5	92.2 (4)
O2 ⁱ —Te1—O1	93.5 (4)	O7—X1—O8	110.8 (5)
O3 ⁱ —Te1—O1	88.7 (4)	O7—X1—O9	107.3 (4)
O3 ⁱ —Te1—O2	91.5 (4)	O8—X1—O9	108.6 (5)
O4 ⁱⁱ —Te2—O6 ⁱⁱ	87.9 (4)	O7—X1—O10	108.1 (5)
O4 ⁱⁱ —Te2—O5 ⁱⁱ	88.5 (3)	O8—X1—O10	108.6 (5)
O6 ⁱⁱ —Te2—O5 ⁱⁱ	87.8 (4)	O9—X1—O10	113.4 (5)

Symmetry codes: (i) $-x, -y, -z + 1$; (ii) $-x + 1, -y + 1, -z + 1$; (iii) $-x + 1, y - \frac{1}{2}, -z + \frac{1}{2}$; (iv) $-x + 1, y + \frac{1}{2}, -z + \frac{1}{2}$; (v) $x + 1, y, z$; (vi) $-x + 1, -y, -z$; (vii) $x + 1, -y + \frac{1}{2}, z - \frac{1}{2}$; (viii) $x, -y + \frac{1}{2}, z - \frac{1}{2}$; (ix) $x, y + 1, z$; (x) $x + 1, y + 1, z$; (xi) $-x + 1, y + \frac{3}{2}, -z + \frac{1}{2}$.

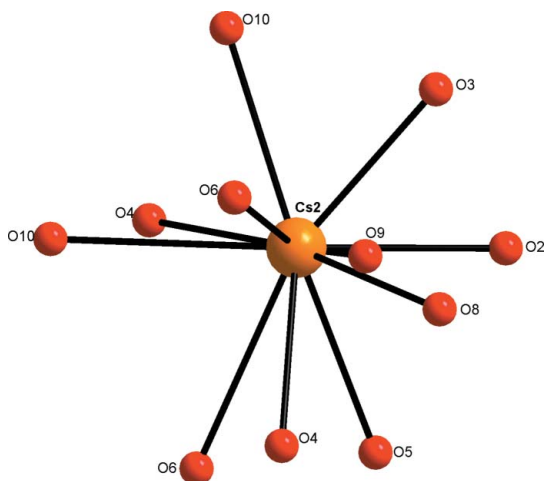


Figure 4
The coordination of Cs2.

For the refinement of the occupation factors for S and Se, their sum was restrained to be equal to 1. The highest peak is situated 1.00 Å from Cs2, and the deepest hole 0.63 Å from S/Se. H atoms could not be located.

Data collection: *COLLECT* (Nonius, 2001); cell refinement: *DENZO* (Otwinowski & Minor, 1997); data reduction: *DENZO*;

program(s) used to solve structure: *SHELXS86* (Sheldrick, 1985); program(s) used to refine structure: *CRYSTALS* (Betteridge *et al.*, 2003); molecular graphics: *DIAMOND* (Brandenburg & Berndt, 1999); software used to prepare material for publication: *CRYSTALS*.

References

- Abdelhedi, M., Dammak, M., Cousson, A. & Kolsi, A. W. (2005). *J. Alloys Compd.* **398**, 55–61.
- Betteridge, P. W., Carruthers, J. R., Cooper, R. I., Prout, K. & Watkin, D. J. (2003). *J. Appl. Cryst.* **36**, 1487.
- Brandenburg, K. & Berndt, M. (1999). *DIAMOND*. Version 2.1.b. Crystal Impact GbR, Bonn, Germany.
- Dammak, M., Mhiri, T., Jaud, J. & Savariault, J. M. (2001). *Int. J. Inorg. Mater.* **3**, 861–873.
- Larson, A. C. (1970). *Crystallographic Computing*, edited by F. R. Ahmed, S. R. Hall & C. P. Huber, p. 29. Copenhagen: Munksgaard.
- Nonius (2001). *COLLECT*. Nonius BV, Delft, The Netherlands.
- Otwinowski, Z. & Minor, W. (1997). *Methods in Enzymology*, Vol. 276, *Macromolecular Crystallography, Part A*, edited by C. W. Carter Jr & R. M. Sweet, pp. 307–326. New York: Academic Press.
- Prince, E. (1982). *Mathematical Techniques in Crystallography and Materials Science*. New York: Springer-Verlag.
- Sheldrick, G. M. (1985). *SHELXS86*. University of Göttingen, Germany.
- Spek, A. L. (2003). *PLATON*. University of Utrecht, The Netherlands.
- Watkin, D. J. (1994). *Acta Cryst.* **A50**, 411–437.
- Zilber, R., Durif, A. & Averbuch-Pouchot, M. T. (1980). *Acta Cryst.* **B36**, 2743–2745.
- Zilber, R., Durif, A. & Averbuch-Pouchot, M. T. (1982). *Acta Cryst.* **B38**, 1554–1556.